

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

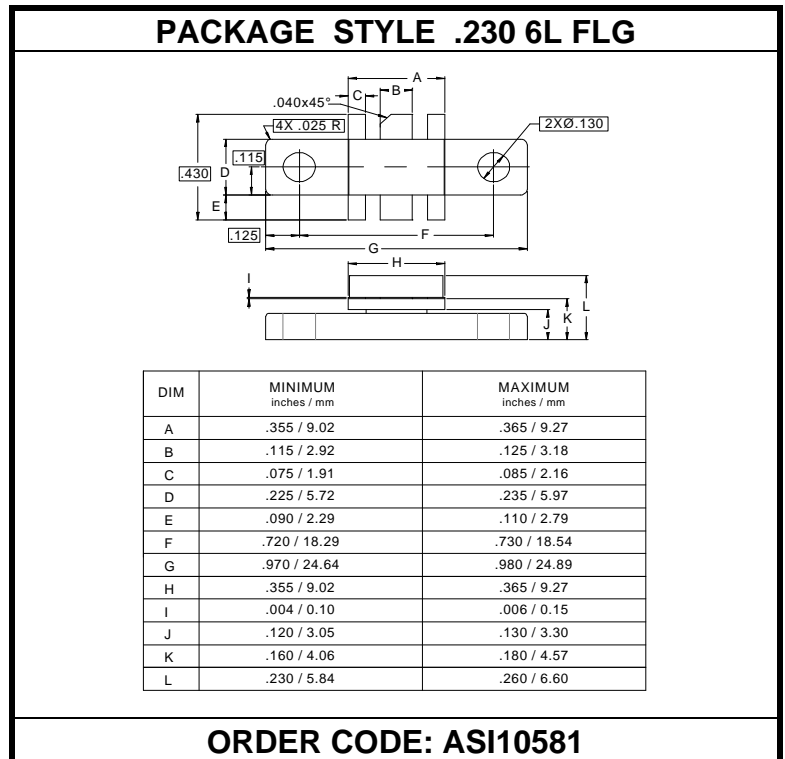
The ASI CBSL15 is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.5 A
V_{CB0}	48 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	29 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	6.0 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 50 mA	48			V
BV_{CEO}	I _C = 20 mA	25			V
BV_{EBO}	I _E = 5 mA	3.5	4.0	---	V
I_{CB0}	V _{CB} = 24 V			1.0	mA
h_{FE}	V _{CE} = 10 V I _C = 100 mA	20		100	---
C_{OB}	V _{CB} = 24 V f = 1.0 MHz			25	pF
P_G η_C	V _{CC} = 24 V I _{CQ} = 75 mA f = 960 MHz P _{OUT} = 15 W	8.0	50		dB %